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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	100MHz
Connectivity	I²C, IrDA, LINbus, MMC/SD/SDIO, SPI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, I²S, POR, PWM, WDT
Number of I/O	36
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	128K x 8
Voltage - Supply (Vcc/Vdd)	1.7V ~ 3.6V
Data Converters	A/D 10x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	48-UFQFN Exposed Pad
Supplier Device Package	48-UFQFPN (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f411ccu6tr

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3.15 Power supply supervisor

3.15.1 Internal reset ON

This feature is available for V_{DD} operating voltage range 1.8 V to 3.6 V.

The internal power supply supervisor is enabled by holding PDR_ON high.

The devices have an integrated power-on reset (POR) / power-down reset (PDR) circuitry coupled with a Brownout reset (BOR) circuitry. At power-on, POR is always active, and ensures proper operation starting from 1.8 V. After the 1.8 V POR threshold level is reached, the option byte loading process starts, either to confirm or modify default thresholds, or to disable BOR permanently. Three BOR thresholds are available through option bytes.

The devices remain in reset mode when V_{DD} is below a specified threshold, $V_{POR/PDR}$ or V_{BOR}, without the need for an external reset circuit.

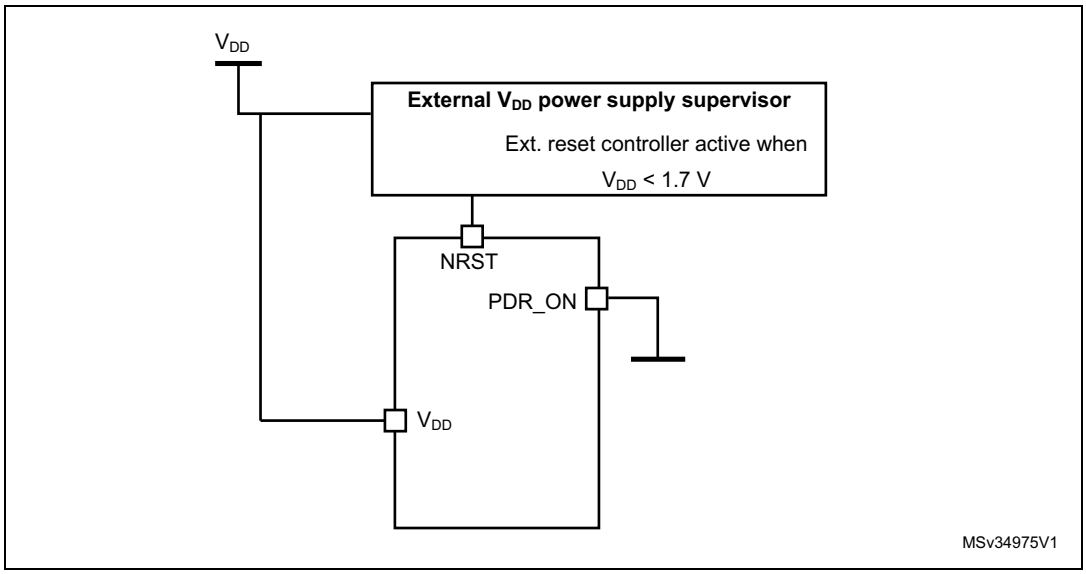
The devices also feature an embedded programmable voltage detector (PVD) that monitors the V_{DD}/V_{DDA} power supply and compares it to the V_{PVD} threshold. An interrupt can be generated when V_{DD}/V_{DDA} drops below the V_{PVD} threshold and/or when V_{DD}/V_{DDA} is higher than the V_{PVD} threshold. The interrupt service routine can then generate a warning message and/or put the MCU into a safe state. The PVD is enabled by software.

3.15.2 Internal reset OFF

This feature is available only on packages featuring the PDR_ON pin. The internal power-on reset (POR) / power-down reset (PDR) circuitry is disabled by setting the PDR_ON pin to low.

An external power supply supervisor should monitor V_{DD} and should set the device in reset mode when V_{DD} is below 1.7 V. NRST should be connected to this external power supply supervisor. Refer to *Figure 5: Power supply supervisor interconnection with internal reset OFF*.

Figure 5. Power supply supervisor interconnection with internal reset OFF(1)



1. The PRD_ON pin is only available on the WLCSP49 and UFBGA100 packages.

3.20.5 SysTick timer

This timer is dedicated to real-time operating systems, but could also be used as a standard downcounter. It features:

- A 24-bit downcounter
- Autoreload capability
- Maskable system interrupt generation when the counter reaches 0
- Programmable clock source.

3.21 Inter-integrated circuit interface (I^2C)

Up to three I^2C bus interfaces can operate in multimaster and slave modes. They can support the standard (up to 100 kHz) and fast (up to 400 kHz) modes. The I2C bus frequency can be increased up to 1 MHz. For more details about the complete solution, please contact your local ST sales representative.They also support the 7/10-bit addressing mode and the 7-bit dual addressing mode (as slave). A hardware CRC generation/verification is embedded.

They can be served by DMA and they support SMBus 2.0/PMBus.

The devices also include programmable analog and digital noise filters (see *Table 5*).

Table 5. Comparison of I2C analog and digital filters

	Analog filter	Digital filter
Pulse width of suppressed spikes	≥ 50 ns	Programmable length from 1 to 15 I2C peripheral clocks

3.22 Universal synchronous/asynchronous receiver transmitters (USART)

The devices embed three universal synchronous/asynchronous receiver transmitters (USART1, USART2 and USART6).

These three interfaces provide asynchronous communication, IrDA SIR ENDEC support, multiprocessor communication mode, single-wire half-duplex communication mode and have LIN Master/Slave capability. The USART1 and USART6 interfaces are able to communicate at speeds of up to 12.5 Mbit/s. The USART2 interface communicates at up to 6.25 bit/s.

USART1 and USART2 also provide hardware management of the CTS and RTS signals, Smart Card mode (ISO 7816 compliant) and SPI-like communication capability. All interfaces can be served by the DMA controller.

Table 8. STM32F411xC/xE pin definitions (continued)

Pin number					Pin name (function after reset)(1)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
UFQFPN48	LQFP64	WLCSP49	LQFP100	UFBGA100						
31	43	C2	69	C12	PA10	I/O	FT	-	TIM1_CH3, SPI5_MOSI/I2S5_SD, USART1_RX, USB_FS_ID, EVENTOUT	-
32	44	C1	70	B12	PA11	I/O	FT	-	TIM1_CH4, SPI4_MISO, USART1_CTS, USART6_TX, USB_FS_DM, EVENTOUT	-
33	45	C3	71	A12	PA12	I/O	FT	-	TIM1_ETR, SPI5_MISO, USART1_RTS, USART6_RX, USB_FS_DP, EVENTOUT	-
34	46	B3	72	A11	PA13	I/O	FT	-	JTMS-SWDIO, EVENTOUT	-
-	-	-	73	C11	VCAP_2	S	-	-	-	-
35	47	B1	74	F11	VSS	S	-	-	-	-
36	48	B2	75	G11	VDD	S	-	-	-	-
37	49	A1	76	A10	PA14	I/O	FT	-	JTCK-SWCLK, EVENTOUT	-
38	50	A2	77	A9	PA15	I/O	FT	-	JTDI, TIM2_CH1/TIM2_ETR, SPI1_NSS/I2S1_WS, SPI3_NSS/I2S3_WS, USART1_TX, EVENTOUT	-
-	51	-	78	B11	PC10	I/O	FT	-	SPI3_SCK/I2S3_CK, SDIO_D2, EVENTOUT	-
-	52	-	79	C10	PC11	I/O	FT	-	I2S3ext_SD, SPI3_MISO, SDIO_D3, EVENTOUT	-
-	53	-	80	B10	PC12	I/O	FT	-	SPI3_MOSI/I2S3_SD, SDIO_CK, EVENTOUT	-

6.3.5 Embedded reset and power control block characteristics

The parameters given in *Table 19* are derived from tests performed under ambient temperature and V_{DD} supply voltage @ 3.3V.

Table 19. Embedded reset and power control block characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{PVD}	Programmable voltage detector level selection	PLS[2:0]=000 (rising edge)	2.09	2.14	2.19	V
		PLS[2:0]=000 (falling edge)	1.98	2.04	2.08	
		PLS[2:0]=001 (rising edge)	2.23	2.30	2.37	
		PLS[2:0]=001 (falling edge)	2.13	2.19	2.25	
		PLS[2:0]=010 (rising edge)	2.39	2.45	2.51	
		PLS[2:0]=010 (falling edge)	2.29	2.35	2.39	
		PLS[2:0]=011 (rising edge)	2.54	2.60	2.65	
		PLS[2:0]=011 (falling edge)	2.44	2.51	2.56	
		PLS[2:0]=100 (rising edge)	2.70	2.76	2.82	
		PLS[2:0]=100 (falling edge)	2.59	2.66	2.71	
		PLS[2:0]=101 (rising edge)	2.86	2.93	2.99	
		PLS[2:0]=101 (falling edge)	2.77	2.82	2.89	
		PLS[2:0]=110 (rising edge)	2.96	3.03	3.10	
		PLS[2:0]=110 (falling edge)	2.85	2.93	2.99	
		PLS[2:0]=111 (rising edge)	3.07	3.14	3.21	
		PLS[2:0]=111 (falling edge)	2.95	3.03	3.09	
$V_{PVDhyst}$(2)	PVD hysteresis	-	-	100	-	mV
$V_{POR/PDR}$	Power-on/power-down reset threshold	Falling edge	1.60(1)	1.68	1.76	V
		Rising edge	1.64	1.72	1.80	
$V_{PDRhyst}$(2)	PDR hysteresis	-	-	40	-	mV
V_{BOR1}	Brownout level 1 threshold	Falling edge	2.13	2.19	2.24	V
		Rising edge	2.23	2.29	2.33	
V_{BOR2}	Brownout level 2 threshold	Falling edge	2.44	2.50	2.56	
		Rising edge	2.53	2.59	2.63	
V_{BOR3}	Brownout level 3 threshold	Falling edge	2.75	2.83	2.88	
		Rising edge	2.85	2.92	2.97	
$V_{BORhyst}$(2)	BOR hysteresis	-	-	100	-	mV
$T_{RSTTEMPO}$(2)(3)	POR reset timing	-	0.5	1.5	3.0	ms

Table 26. Typical and maximum current consumption in Sleep mode - V_{DD} = 3.6 V

Symbol	Parameter	Conditions	f_{HCLK} (MHz)	Typ	Max(1)				Unit
					T_A = 25 °C	T_A = 85 °C	T_A = 105 °C	T_A = 125 °C	
I_{DD}	Supply current in **Sleep mode**	External clock, PLL ON(2), all peripherals enabled(3)(4)	100	12.2	13.2	13.4	14.1	15.3	mA
			84	9.8	10.6	10.9	11.6	12.8	
			64	6.9	7.4	7.7	8.3	9.5	
			50	5.4	5.9	6.2	6.8	8.0	
			20	2.8	3.2	3.5	4.1	5.3	
		HSI, PLL OFF(2), all peripherals enabled(3)	16	1.3	1.7	2.2	2.8	4.0	
			1	0.4	0.5	0.9	1.6	2.8	
		External clock, PLL ON(2) all peripherals disabled(3)	100	3.0	3.6	3.9	4.5	5.7	
			84	2.5	3.0	3.2	3.9	5.1	
			64	1.9	2.2	2.5	3.0	4.2	
			50	1.6	1.9	2.1	2.7	3.9	
			20	1.1	1.4	1.7	2.3	3.5	
		HSI, PLL OFF(2), all peripherals disabled(3)	16	0.4	0.5	0.9	1.6	2.8	
			1	0.3	0.4	0.8	1.5	2.7	

1. Guaranteed by characterization results.
2. Refer to *Table 41* and RM0383 for the possible PLL VCO setting.
3. Add an additional power consumption of 1.6 mA per ADC for the analog part. In applications, this consumption occurs only while the ADC is ON (ADON bit is set in the ADC_CR2 register).
4. When the ADC is ON (ADON bit set in the ADC_CR2), add an additional power consumption of 1.6mA per ADC for the analog part.

Table 27. Typical and maximum current consumptions in Stop mode - V_{DD} = 1.7 V

Symbol	Conditions	Parameter	Typ(1)	Max(1)				Unit
			T_A = 25 °C	T_A = 25 °C	T_A = 85 °C	T_A = 105 °C	T_A = 125 °C	
I_{DD_STOP}	Flash in Stop mode, all oscillators OFF, no independent watchdog	Main regulator usage	112	142(2)	400	710(2)	1200	µA
		Low power regulator usage	42.6	67(2)	300	580(2)	1044	
	Flash in Deep power down mode, all oscillators OFF, no independent watchdog	Main regulator usage	75	99(2)	310	580(2)	993	
		Low power regulator usage	13.6	37(2)	265	550(2)	1007	
		Low power low voltage regulator usage	9	28(2)	230	500(2)	910	

1. Guaranteed by characterization results.
2. Guaranteed by test in production.

Table 28. Typical and maximum current consumption in Stop mode - V_{DD}=3.6 V

Symbol	Conditions	Parameter	Typ	Max(1)				Unit
			T_A = 25 °C	T_A = 25 °C	T_A = 85 °C	T_A = 105 °C	T_A = 125 °C	
I_{DD_STOP}	Flash in Stop mode, all oscillators OFF, no independent watchdog	Main regulator usage	113.7	145(2)	410	720(2)	1217	µA
		Low power regulator usage	43.1	68(2)	310	600(2)	1073	
	Flash in Deep power down mode, all oscillators OFF, no independent watchdog	Main regulator usage	76.2	105(2)	320	600(2)	1019	
		Low power regulator usage	14	38(2)	275	560(2)	1025	
		Low power low voltage regulator usage	10	30(2)	235	510(2)	928	

1. Guaranteed by characterization results.
2. Guaranteed by test in production.

Table 29. Typical and maximum current consumption in Standby mode - V_{DD}= 1.7 V

Symbol	Parameter	Conditions	Typ(1)	Max(2)				Unit
			T_A = 25 °C	T_A = 25 °C	T_A = 85 °C	T_A = 105 °C	T_A = 125 °C	
I_{DD_STBY}	Supply current in Standby mode	Low-speed oscillator (LSE) and RTC ON	2.4	4	12	25	50	µA
		RTC and LSE OFF	1.8	3(3)	11	24(3)	49	

1. When the PDR is OFF (internal reset is OFF), the typical current consumption is reduced by 1.2 µA.
2. Guaranteed by characterization results.
3. Guaranteed by test in production.

Table 30. Typical and maximum current consumption in Standby mode - V_{DD}= 3.6 V

Symbol	Parameter	Conditions	Typ(1)	Max(2)				Unit
			T_A = 25 °C	T_A = 25 °C	T_A = 85 °C	T_A = 105 °C	T_A = 125 °C	
I_{DD_STBY}	Supply current in Standby mode	Low-speed oscillator (LSE) and RTC ON	2.8	5	14	29	59	µA
		RTC and LSE OFF	2.1	4(3)	13.5	28(3)	58	

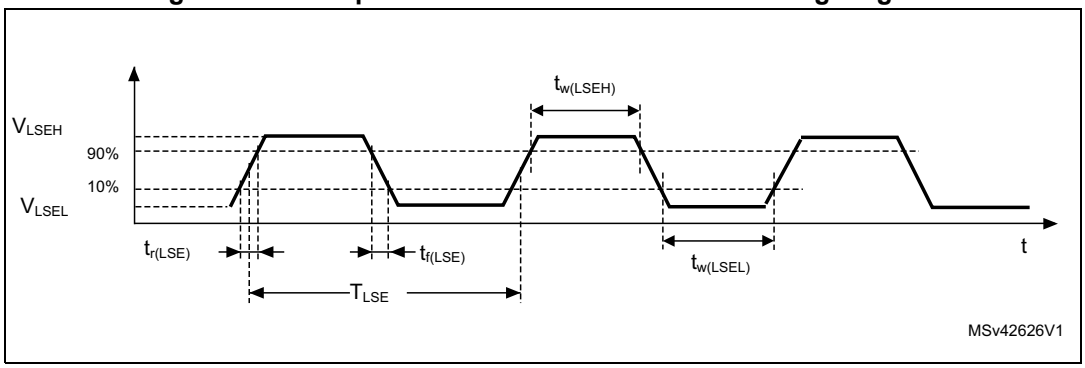
1. When the PDR is OFF (internal reset is OFF), the typical current consumption is reduced by 1.2 µA.
2. Guaranteed by characterization results.
3. Guaranteed by test in production.

Table 32. Switching output I/O current consumption

Symbol	Parameter	Conditions[1]	I/O toggling frequency (f_{SW})	Typ	Unit
IDDIO	I/O switching current	V_{DD} = 3.3 V C = C_{INT}	2 MHz	0.05	mA
			8 MHz	0.15	
			25 MHz	0.45	
			50 MHz	0.85	
			60 MHz	1.00	
			84 MHz	1.40	
			90 MHz	1.67	
		V_{DD} = 3.3 V C_{EXT} = 0 pF C = C_{INT} + C_{EXT} + C_S	2 MHz	0.10	
			8 MHz	0.35	
			25 MHz	1.05	
			50 MHz	2.20	
			60 MHz	2.40	
			84 MHz	3.55	
			90 MHz	4.23	
		V_{DD} = 3.3 V C_{EXT} =10 pF C = C_{INT} + C_{EXT} + C_S	2 MHz	0.20	
			8 MHz	0.65	
			25 MHz	1.85	
			50 MHz	2.45	
			60 MHz	4.70	
			84 MHz	8.80	
			90 MHz	10.47	
		V_{DD} = 3.3 V C_{EXT} = 22 pF C = C_{INT} + C_{EXT} + C_S	2 MHz	0.25	
			8 MHz	1.00	
			25 MHz	3.45	
			50 MHz	7.15	
			60 MHz	11.55	
		V_{DD} = 3.3 V C_{EXT} = 33 pF C = C_{INT} + C_{EXT} + C_S	2 MHz	0.32	
			8 MHz	1.27	
			25 MHz	3.88	
			50 MHz	12.34	

1. CS is the PCB board capacitance including the pad pin. CS = 7 pF (estimated value).

Figure 23. Low-speed external clock source AC timing diagram



High-speed external clock generated from a crystal/ceramic resonator

The high-speed external (HSE) clock can be supplied with a 4 to 26 MHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on characterization results obtained with typical external components specified in *Table 37*. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Table 37. HSE 4-26 MHz oscillator characteristics(1)

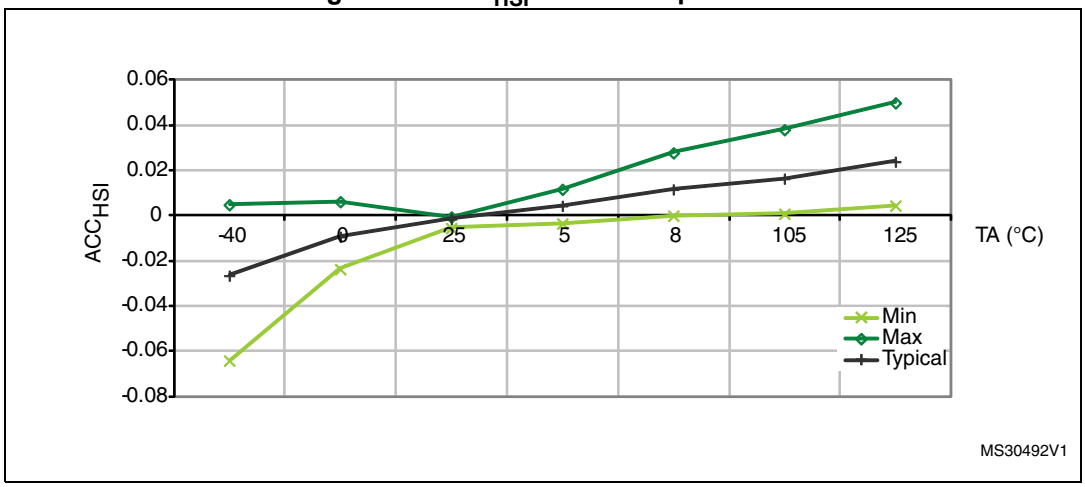
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{OSC_IN}	Oscillator frequency		4	-	26	MHz
R_F	Feedback resistor		-	200	-	kΩ
I_{DD}	HSE current consumption	V_{DD}=3.3 V, ESR= 30 Ω, C_L=5 pF @25 MHz	-	450	-	µA
		V_{DD}=3.3 V, ESR= 30 Ω, C_L=10 pF @25 MHz	-	530	-	
$G_{m\_crit\_max}$	Maximum critical crystal g_m	Startup	-	-	1	mA/V
$t_{SU(HSE)}$(2)	Startup time	V_{DD} is stabilized	-	2	-	ms

1. Guaranteed by design.
2. $t_{SU(HSE)}$ is the startup time measured from the moment it is enabled (by software) to a stabilized 8 MHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer

For C_{L1} and C_{L2}, it is recommended to use high-quality external ceramic capacitors in the 5 pF to 25 pF range (Typ.), designed for high-frequency applications, and selected to match the requirements of the crystal or resonator (see *Figure 24*). C_{L1} and C_{L2} are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of C_{L1} and C_{L2}. PCB and MCU pin capacitance must be included (10 pF can be used as a rough estimate of the combined pin and board capacitance) when sizing C_{L1} and C_{L2}.

Note: For information on selecting the crystal, refer to the application note AN2867 "Oscillator design guide for ST microcontrollers" available from the ST website www.st.com.

Figure 26. ACC_{HSI} versus temperature



1. Guaranteed by characterization results.

Low-speed internal (LSI) RC oscillator

Table 40. LSI oscillator characteristics (1)

Symbol	Parameter	Min	Typ	Max	Unit
f_{LSI}(2)	Frequency	17	32	47	kHz
$t_{su(LSI)}$(3)	LSI oscillator startup time	-	15	40	µs
$I_{DD(LSI)}$(3)	LSI oscillator power consumption	-	0.4	0.6	µA

1. V_{DD} = 3 V, T_A = –40 to 125 °C unless otherwise specified.
2. Guaranteed by characterization results.
3. Guaranteed by design.

Note: It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative currents.

6.3.16 I/O port characteristics

General input/output characteristics

Unless otherwise specified, the parameters given in *Table 53* are derived from tests performed under the conditions summarized in *Table 14*. All I/Os are CMOS and TTL compliant.

Table 53. I/O static characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{IL}	FT, TC and NRST I/O input low level voltage	1.7 V≤V_{DD}≤3.6 V	-	-	0.3V_{DD}(1)	V
	BOOT0 I/O input low level voltage	1.75 V≤V_{DD} ≤3.6 V, -40 °C≤T_A ≤125 °C	-	-	0.1V_{DD}+0.1(2)	
		1.7 V≤V_{DD} ≤3.6 V, 0 °C≤T_A ≤125 °C	-	-		
V_{IH}	FT, TC and NRST I/O input high level voltage(5)	1.7 V≤V_{DD}≤3.6 V	0.7V_{DD}(1)	-	-	V
	BOOT0 I/O input high level voltage	1.75 V≤V_{DD} ≤3.6 V, -40 °C≤T_A ≤125 °C	0.17V_{DD} +0.7(2)	-	-	
		1.7 V≤V_{DD} ≤3.6 V, 0 °C≤T_A ≤125 °C				
V_{HYS}	FT, TC and NRST I/O input hysteresis	1.7 V≤V_{DD}≤3.6 V	-	10% V_{DD}(3)	-	V
	BOOT0 I/O input hysteresis	1.75 V≤V_{DD} ≤3.6 V, -40 °C≤T_A ≤125 °C	-	100	-	mV
		1.7 V≤V_{DD} ≤3.6 V, 0 °C≤T_A ≤125 °C				
I_{lkg}	I/O input leakage current (4)	V_{SS} ≤V_{IN} ≤V_{DD}	-	-	±1	µA
	I/O FT/TC input leakage current (5)	V_{IN} = 5 V	-	-	3	

Table 60. SPI dynamic characteristics(1) (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$t_{a(SO)}$	Data output access time	Slave mode	7	-	21	ns
$t_{dis(SO)}$	Data output disable time	Slave mode	5	-	12	ns
$t_{v(SO)}$	Data output valid time	Slave mode (after enable edge), 2.7 V < V_{DD} < 3.6 V	-	11	13	ns
		Slave mode (after enable edge), 1.7 V < V_{DD} < 3.6 V	-	11	18.5	ns
$t_{h(SO)}$	Data output hold time	Slave mode (after enable edge), 1.7 V < V_{DD} < 3.6 V	8	-	-	ns
$t_{v(MO)}$	Data output valid time	Master mode (after enable edge)	-	4	6	ns
$t_{h(MO)}$	Data output hold time	Master mode (after enable edge)	0	-	-	ns

1. Guaranteed by characterization results.
2. Maximum frequency in Slave transmitter mode is determined by the sum of $t_{v(SO)}$ and $t_{su(MI)}$ which has to fit into SCK low or high phase preceding the SCK sampling edge. This value can be achieved when the SPI communicates with a master having $t_{su(MI)}$ = 0 while Duty(SCK) = 50%

Figure 34. SPI timing diagram - slave mode and CPHA = 0

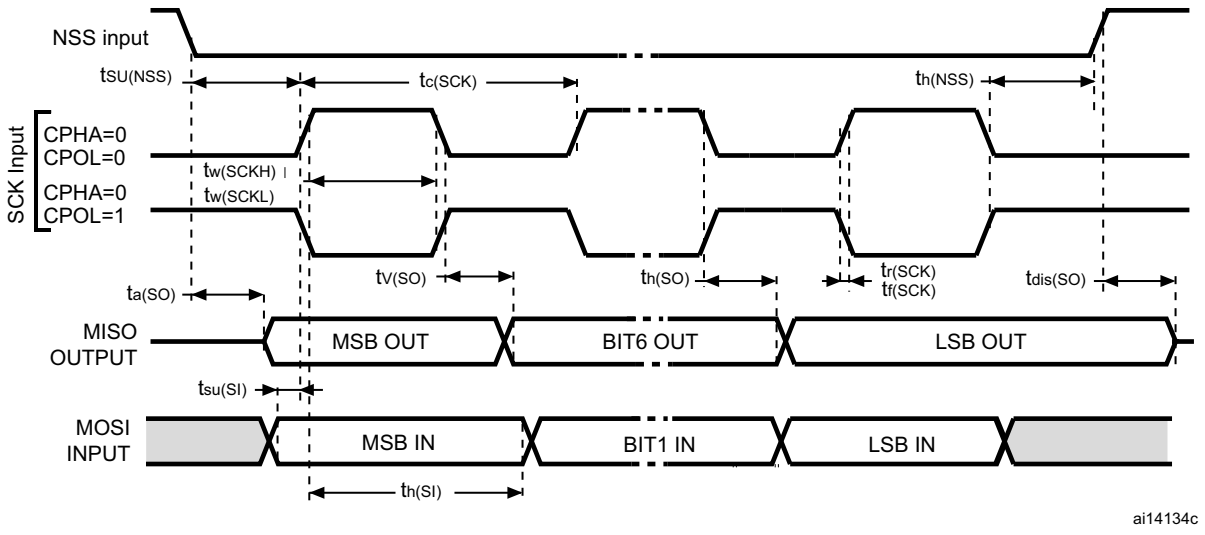


Figure 39. USB OTG FS timings: definition of data signal rise and fall time

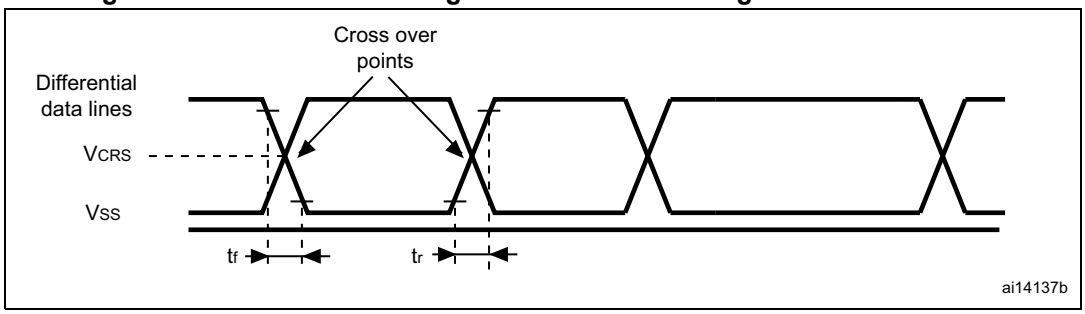


Table 64. USB OTG FS electrical characteristics(1)

Driver characteristics					
Symbol	**Parameter**	**Conditions**	**Min**	**Max**	**Unit**
t_r	Rise time(2)	C_L = 50 pF	4	20	ns
t_f	Fall time(2)	C_L = 50 pF	4	20	ns
t_{rfm}	Rise/ fall time matching	t_r/t_f	90	110	%
V_{CRS}	Output signal crossover voltage		1.3	2.0	V

1. Guaranteed by design.
2. Measured from 10% to 90% of the data signal. For more detailed informations, please refer to USB Specification - Chapter 7 (version 2.0).

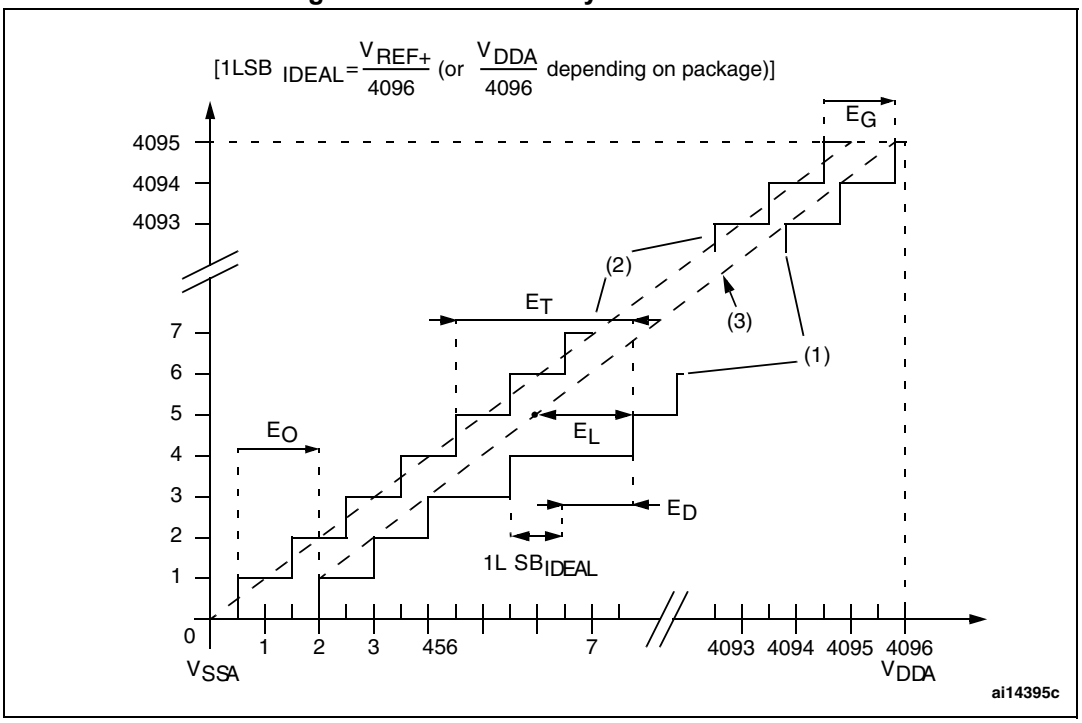
6.3.20 12-bit ADC characteristics

Unless otherwise specified, the parameters given in *Table 65* are derived from tests performed under the ambient temperature, f_{PCLK2} frequency and V_{DDA} supply voltage conditions summarized in *Table 14*.

Table 65. ADC characteristics

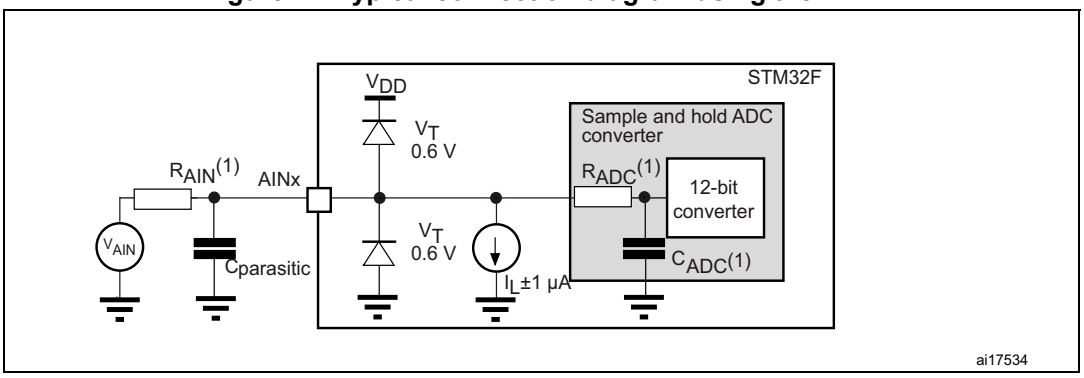
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DDA}	Power supply	$V_{DDA} - V_{REF+} < 1.2$ V	1.7(1)	-	3.6	V
V_{REF+}	Positive reference voltage		1.7(1)	-	V_{DDA}	V
f_{ADC}	ADC clock frequency	V_{DDA} = 1.7(1) to 2.4 V	0.6	15	18	MHz
		V_{DDA} = 2.4 to 3.6 V	0.6	30	36	MHz
f_{TRIG}(2)	External trigger frequency	f_{ADC} = 30 MHz, 12-bit resolution	-	-	1764	kHz
			-	-	17	$1/f_{ADC}$
V_{AIN}	Conversion voltage range(3)		0 (V_{SSA} or V_{REF-} tied to ground)	-	V_{REF+}	V
R_{AIN}(2)	External input impedance	See *Equation 1* for details	-	-	50	kΩ
R_{ADC}(2)(4)	Sampling switch resistance		-	-	6	kΩ
C_{ADC}(2)	Internal sample and hold capacitor		-	4	7	pF

Figure 40. ADC accuracy characteristics



1. See also *Table 67*.
2. Example of an actual transfer curve.
3. Ideal transfer curve.
4. End point correlation line.
5. E_T = Total Unadjusted Error: maximum deviation between the actual and the ideal transfer curves.
   EO = Offset Error: deviation between the first actual transition and the first ideal one.
   EG = Gain Error: deviation between the last ideal transition and the last actual one.
   ED = Differential Linearity Error: maximum deviation between actual steps and the ideal one.
   EL = Integral Linearity Error: maximum deviation between any actual transition and the end point correlation line.

Figure 41. Typical connection diagram using the ADC

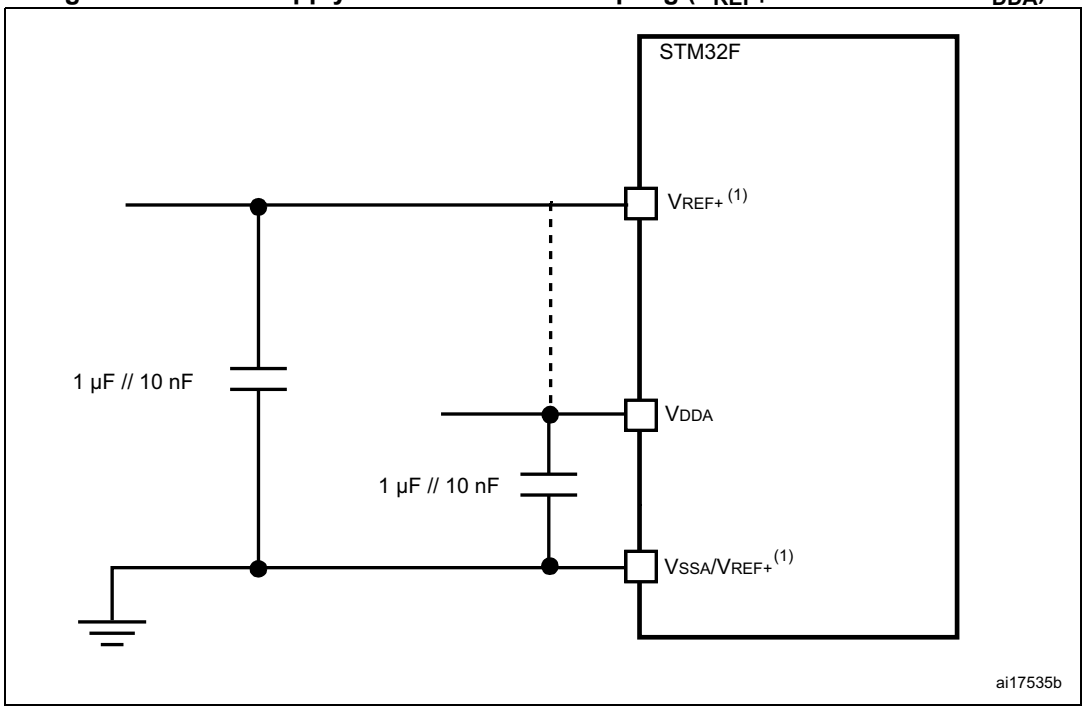


1. Refer to *Table 65* for the values of R_{AIN}, R_{ADC} and C_{ADC}.
2. $C_{parasitic}$ represents the capacitance of the PCB (dependent on soldering and PCB layout quality) plus the pad capacitance (roughly 5 pF). A high $C_{parasitic}$ value downgrades conversion accuracy. To remedy this, f_{ADC} should be reduced.

General PCB design guidelines

Power supply decoupling should be performed as shown in *Figure 42* or *Figure 43*, depending on whether V_{REF+} is connected to V_{DDA} or not. The 10 nF capacitors should be ceramic (good quality). They should be placed them as close as possible to the chip.

Figure 42. Power supply and reference decoupling (V_{REF+} not connected to V_{DDA})



1. V_{REF+} and V_{REF-} inputs are both available on UFBGA100. V_{REF+} is also available on LQFP100. When V_{REF+} and V_{REF-} are not available, they are internally connected to V_{DDA} and V_{SSA}.

6.3.25 RTC characteristics

Table 77. Dynamic characteristics: eMMC characteristics V_{DD} = 1.7 V to 1.9 V(1)(2)

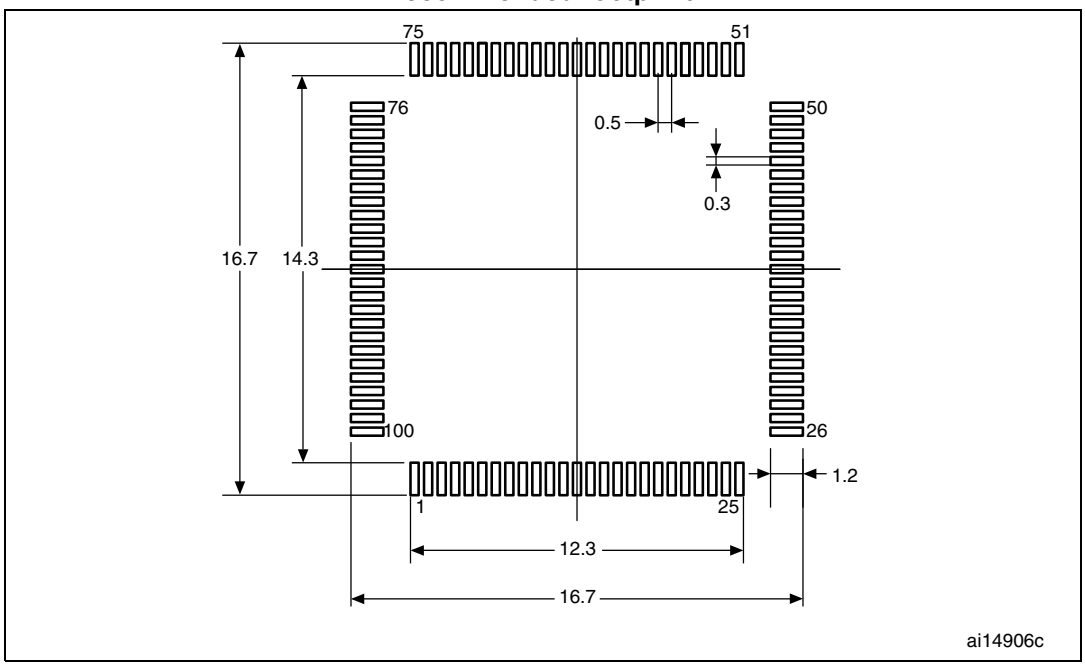
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{PP}	Clock frequency in data transfer mode	-	0	-	50	MHz
-	SDIO_CK/fPCLK2 frequency ratio	-	-	-	8/3	-
$t_{W(CKL)}$	Clock low time	fpp = 50 MHz	10	10.5	-	ns
$t_{W(CKH)}$	Clock high time	fpp = 50 MHz	9	9.5	-	
CMD, D inputs (referenced to CK) in eMMC mode						
t_{ISU}	Input setup time HS	fpp = 50 MHz	0	-	-	ns
t_{IH}	Input hold time HS	fpp = 50 MHz	6	-	-	
CMD, D outputs (referenced to CK) in eMMC mode						
t_{OV}	Output valid time HS	fpp = 50 MHz	-	3.5	5	ns
t_{OH}	Output hold time HS	fpp = 50 MHz	2	-	-	

1. Guaranteed by characterization results.
2. C_{load} = 20 pF

Table 78. RTC characteristics

Symbol	Parameter	Conditions	Min	Max
-	f_{PCLK1}/RTCCLK frequency ratio	Any read/write operation from/to an RTC register	4	-

Figure 56. LQFP100 - 100-pin, 14 x 14 mm, 100-pin low-profile quad flat recommended footprint



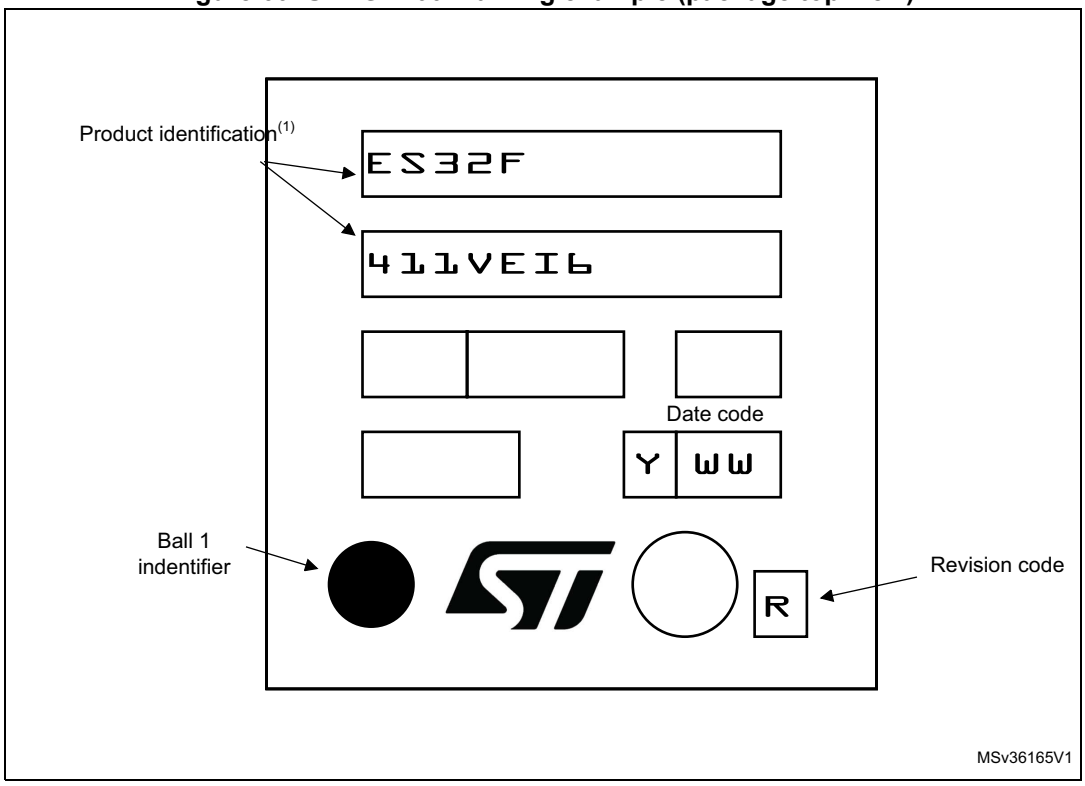
1. Dimensions are in millimeters.

Device marking for UFBGA100

The following figure gives an example of topside marking orientation versus ball A1 identifier location.

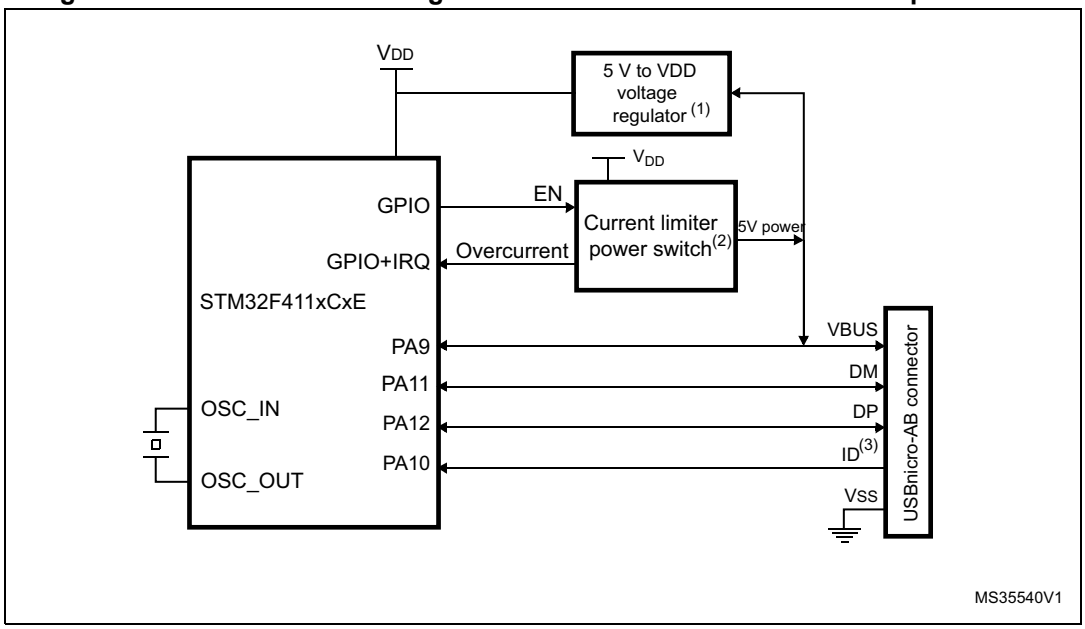
Other optional marking or inset/upset marks, which depend on supply chain operations, are not indicated below.

Figure 60. UFBGA100 marking example (package top view)



1. Parts marked as “ES”, “E” or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

Figure 63. USB controller configured in dual mode and used in Full-Speed mode



1. The external voltage regulator is only needed when building a V_{BUS} powered device.
2. The current limiter is required only if the application has to support a V_{BUS} powered device. A basic power switch can be used if 5 V are available on the application board.
3. The ID pin is required in dual role only.